SKM800GM12M7X



SEMITRANS® 3

IGBT M7 Modules

SKM800GM12M7X

Features*

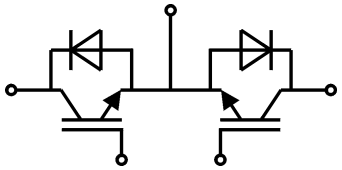
- $V_{CE(sat)}$ with positive temperature coefficient
- High overload capability
- Low loss high density IGBT´s
- Large clearance (10 mm) and creepage distances (20 mm)
- Insulated copper baseplate using DBC Technology (Direct Bonded Copper)
- UL recognized, file no. E63532
- With H_2S protection
- With improved humidity robustness

Typical Applications

- Matrix Inverter
- Bidirectional switch

Remarks

- Max. case temperature limited to T_C = T_S = 125 °C
- Product reliability results are valid for T_j = 150 °C (recommended $T_{j,op}$ = -40...+150 °C)
- For storage and case temperature with TIM see document: "Technical Explanations Thermal Interface Materials"



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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 175 °C	T_c = 25 °C	1098	A
		T_c = 80 °C	830	A
I_{Cnom}			800	A
I_{CRM}			1600	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 800 V V_{GE} ≤ 15 V V_{CES} ≤ 1200 V	T_j = 150 °C	8	µs
T_j			-40 ... 175	°C
Inverse diode				
V_{RRM}	T_j = 25 °C		1200	V
I_F	Continuous DC forward current		800	A
I_{FRM}			1600	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		3700	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$	$T_{Terminal}$ ≤ 90°C, T_C = 90°C		650	A
T_{stg}	module without TIM		-40 ... 125	°C
V_{isol}	AC sinus 50 Hz, t = 1 min		4000	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
$V_{CE(sat)}$	I_C = 800 A V_{GE} = 15 V chiplevel	T_j = 25 °C		1.54	1.88	V
		T_j = 150 °C		1.80		V
V_{CE0}	chiplevel	T_j = 25 °C		0.85	1.02	V
		T_j = 150 °C		0.75		V
r_{CE}	V_{GE} = 15 V chiplevel	T_j = 25 °C		0.86	1.08	mΩ
		T_j = 150 °C		1.31		mΩ
$V_{GE(th)}$	V_{CE} = 10 V, I_C = 80 mA		5.4	6	6.6	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 1200 V, T_j = 25 °C				1	mA
C_{ies}	V_{CE} = 10 V V_{GE} = 0 V	f = 1 MHz		148.0		nF
C_{oes}		f = 1 MHz		4.80		nF
C_{res}		f = 1 MHz		1.68		nF
Q_G	V_{GE} = -8V ... + 15V			7120		nC
R_{Gint}	T_j = 25 °C			0.5		Ω
$t_{d(on)}$	V_{CC} = 600 V I_C = 800 A V_{GE} = +15/-15 V $R_{G\ on}$ = 1.6 Ω $R_{G\ off}$ = 1 Ω di/dt_{on} = 7400 A/µs di/dt_{off} = 6500 A/µs dv/dt = 5800 V/µs	T_j = 150 °C		261		ns
t_r		T_j = 150 °C		117		ns
E_{on}		T_j = 150 °C		74		mJ
$t_{d(off)}$		T_j = 150 °C		494		ns
t_f		T_j = 150 °C		104		ns
E_{off}		T_j = 150 °C		96		mJ
$R_{th(j-c)}$	per IGBT				0.051	K/W
$R_{th(c-s)}$	per IGBT, P12 (reference)			0.035		K/W
$R_{th(c-s)}$	per IGBT, HP-PCM			0.018		K/W

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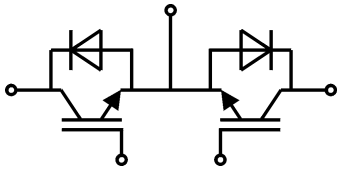
Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	I_F = 800 A V_{GE} = 0 V chiplevel	T_j = 25 °C		1.80	2.10	V
		T_j = 150 °C		1.65		V
V_{F0}	chiplevel	T_j = 25 °C		1.05	1.13	V
		T_j = 150 °C		0.83		V
r_F	chiplevel	T_j = 25 °C		0.94	1.21	mΩ
		T_j = 150 °C		1.03		mΩ
I_{RRM}	I_F = 800 A di/dt_{off} = 7600 A/µs V_{GE} = -15 V V_{CC} = 600 V	T_j = 150 °C		617		A
Q_{rr}		T_j = 150 °C		120		µC
E_{rr}		T_j = 150 °C		53		mJ
$R_{th(j-c)}$	per diode				0.099	K/W
$R_{th(c-s)}$	per diode, P12 (reference)			0.039		K/W
$R_{th(c-s)}$	per diode, HP-PCM			0.022		K/W
Module						
L_{CE}				15		nH
$R_{CC'+EE'}$	measured per switch	T_C = 25 °C		0.4		mΩ
		T_C = 125 °C		0.56		mΩ
$R_{th(c-s)1}$	calculated without thermal coupling, P12 (reference)			0.0092		K/W
$R_{th(c-s)2}$	including thermal coupling, T_s underneath module, P12 (reference)			0.0145		K/W
$R_{th(c-s)}$	including thermal coupling, T_s underneath module, HP-PCM			0.0081		K/W
M_s	to heat sink M6		3		5	Nm
M_t		to terminals M6	2.5		5	Nm
						Nm
w					325	g



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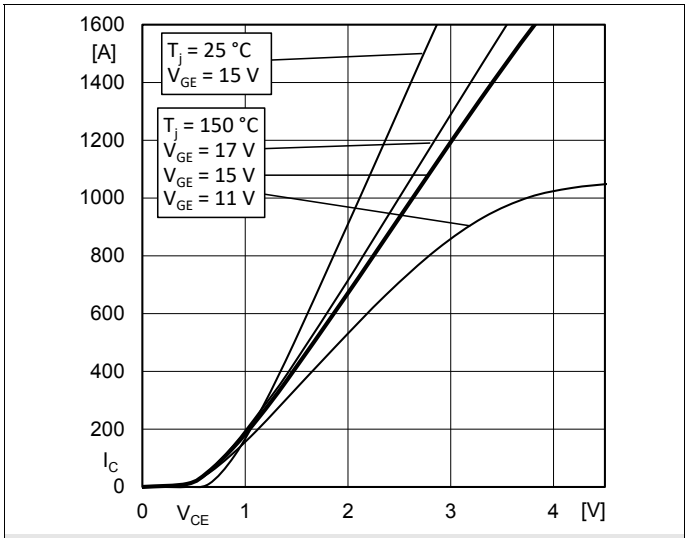

Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

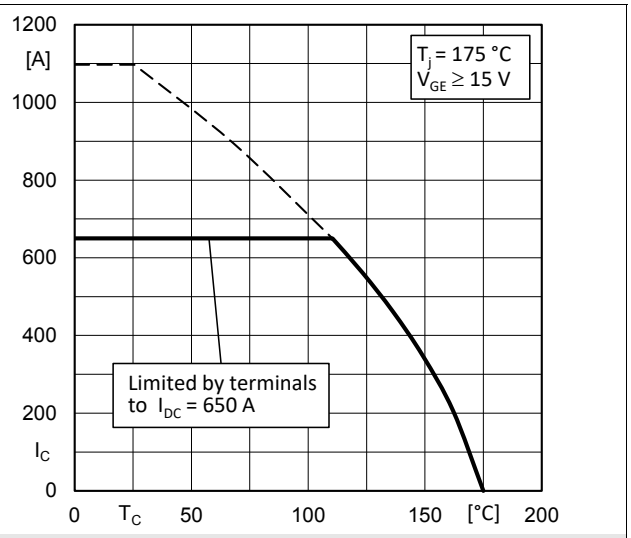

Fig. 2: Rated current vs. temperature $I_c = f(T_c)$

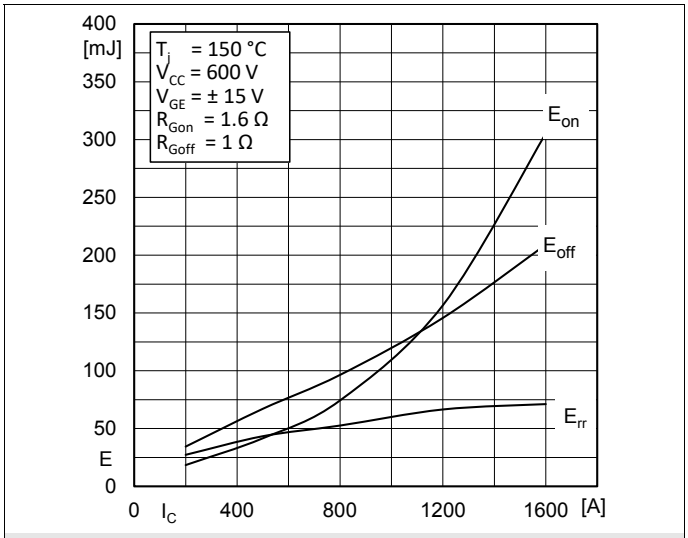

Fig. 3: Typ. turn-on /-off energy = f (I_C)

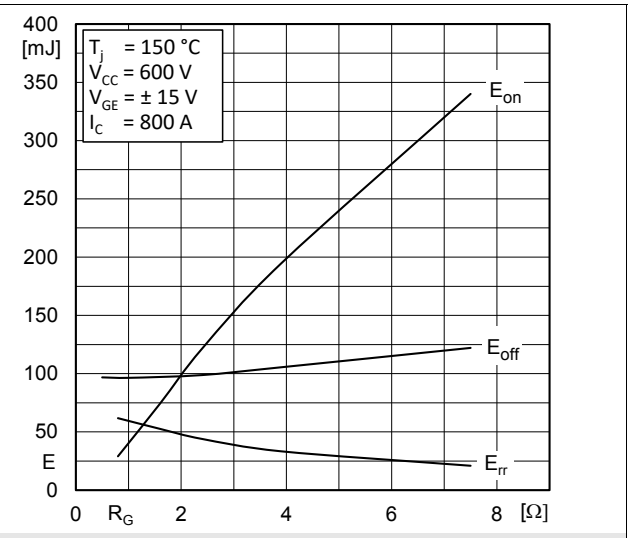

Fig. 4: Typ. turn-on /-off energy = f (R_G)

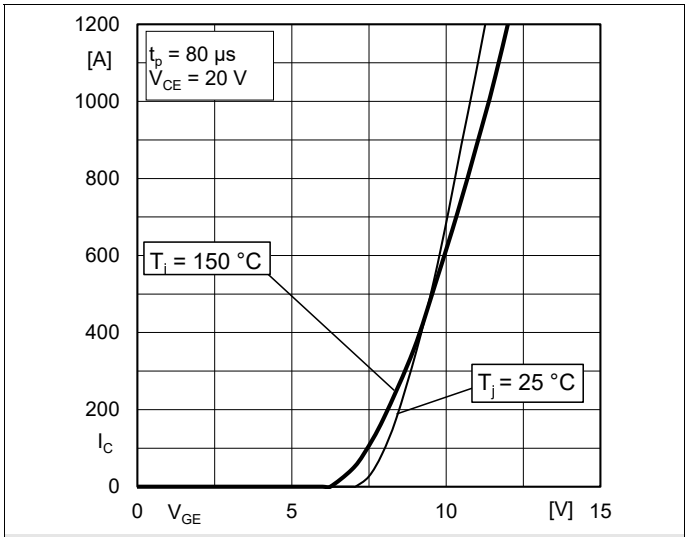

Fig. 5: Typ. transfer characteristic

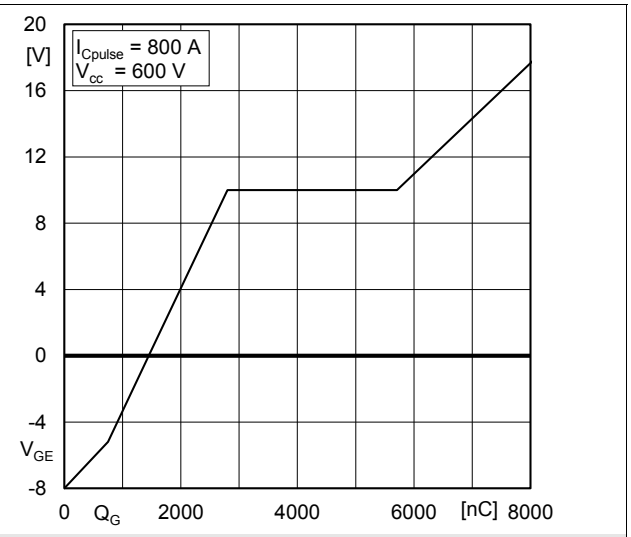

Fig. 6: Typ. gate charge characteristic

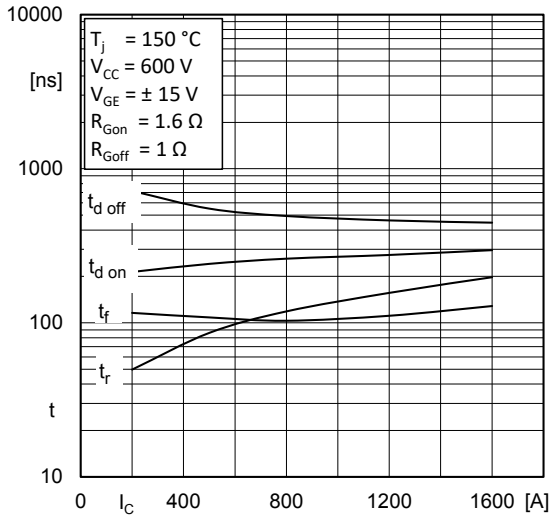

Fig. 7: Typ. switching times vs. I_C

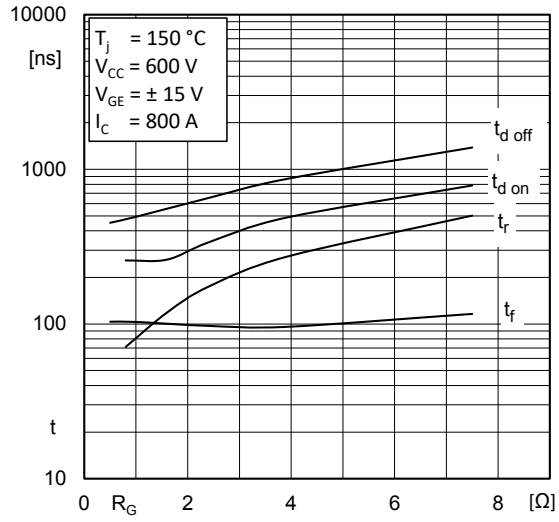

Fig. 8: Typ. switching times vs. gate resistor R_G

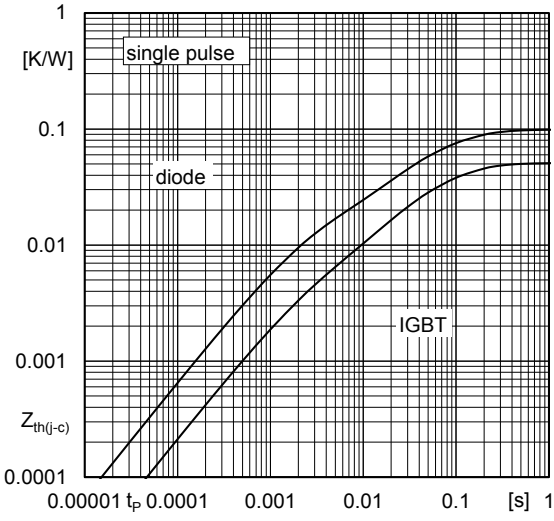

Fig. 9: Transient thermal impedance

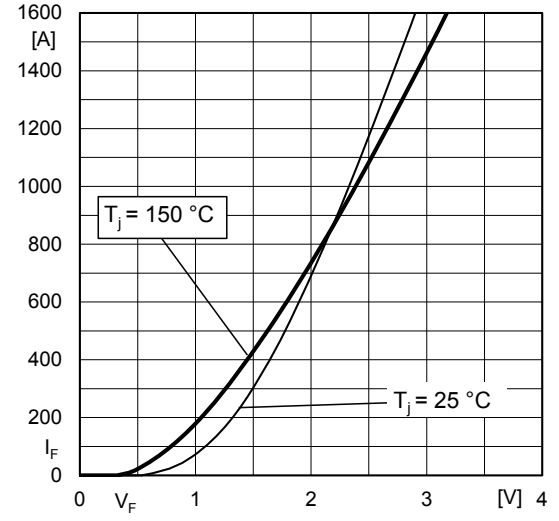

Fig. 10: Typ. diode forward charact., incl. $R_{CC'+EE'}$

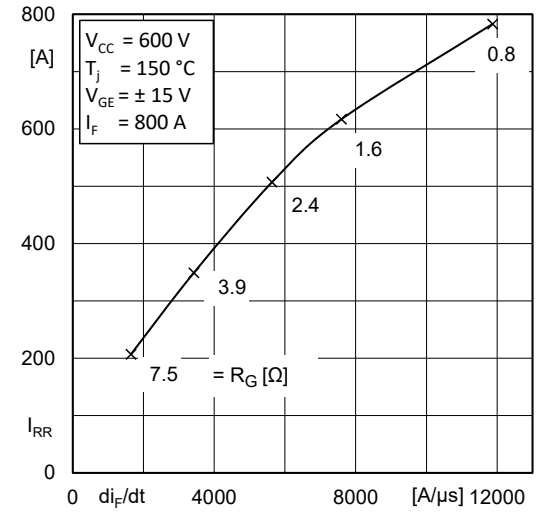

Fig. 11: Typ. diode peak reverse recovery current

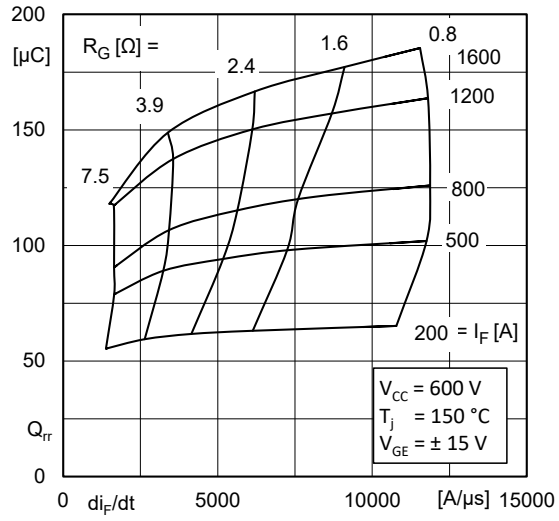

Fig. 12: Typ. diode peak reverse recovery charge

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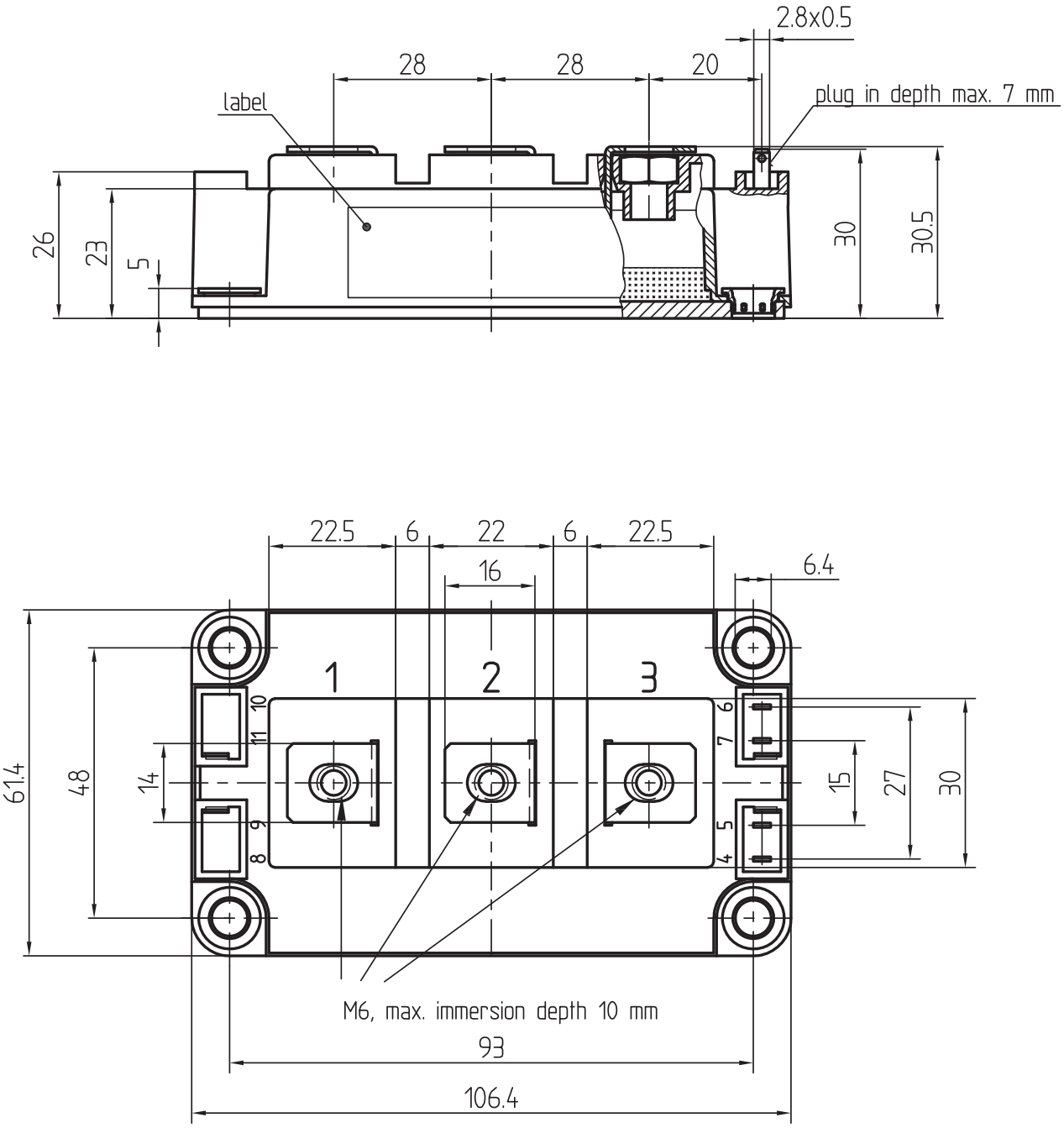
Dimensions in mm



General tolerance +/- 0.5 mm

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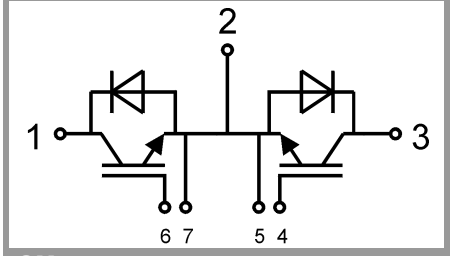

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IMPORTANT INFORMATION AND WARNINGS

This is an electrostatic discharge sensitive device (ESDS) according to international standard IEC 61340.

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